Method for Fabricating a Compound Material and Method For Choosing a Wafer

Abstract

The invention relates to a method for fabricating a compound material wafer, in particular a silicon on insulator type wafer, comprising the steps of providing two wafers andattaching, in particular, bonding the one wafer to the other and wherein in order to reduce the amount of crystalline defects arising on or near the border of the wafer, a step of determining the edge roll off value is carried out, wherein the edge roll off value is determined at about 0.5 - 2.5 mm away from the edge of the wafer and/or determined using the second derivative of the height profiles. The invention also relates to a method for choosing a wafer and to the use of such a wafer in the fabrication process of a compound material wafer

Fig . 3